Docket No.: NIEDERNO EIDE Int. Appl. No.: PCT/DE00/63351

## **CLEAN VERSION OF AMENDED CLAIMS:**

4. (Amended) The thyristor as claimed in claim 2, characterized in that the stop zone (172) is doped more highly in the region (220) lying below the metallization layer (22) of the at least one driver stage (20) than in a region (300) lying below a location (30) for feeding a control current (I) into the cathodal base (16).

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- 5. (Amended) The thyristor as claimed in claim 1, characterized in that the anode short circuits (174), below the metallization layer (22) of the driver stage (20), are at a greater distance (d1) from one another and/or have a smaller diameter (d2) than below the cathode (13) of the thyristor (1).
- 6. (Amended) An arrangement comprising a thyristor (1) as claimed in claim 1 and a diode (4), the thyristor (1) and the diode (4) being electrically connected to one another.